

**Amendment to the Abstract:**

The Abstract has been amended. A revised Abstract is attached.

A semiconductor laser device is provided that includes including: a type a first  
conductivity type, semiconductor substrate of a first conductivity type; a first conductivity type  
cladding layer of the first conductivity type provided on the semiconductor substrate; and an  
active layer provided on the cladding layer. of the first conductivity type, tThe active layer has  
having a super-lattice structure including a disordered region in a vicinity of a at least one  
cavity end face. A; a first cladding layer of a second conductivity type is provided on the active  
layer, an etching stop layer of the second conductivity type is provided on the first cladding  
layer; and a second cladding layer of the second conductivity type is provided on the etching  
stop layer. T, the second cladding layer forming a ridge structure that extends, the ridge  
structure extending along a cavity length direction. An impurity and having a predetermined  
width. A concentration of an impurity in the etching stop layer in the vicinity of the at least one  
cavity end face is greater than a concentration of the impurity in the interior of a cavity and  
equal to or smaller than about  $2 \times 10^{18} \text{ cm}^{-3}$ .